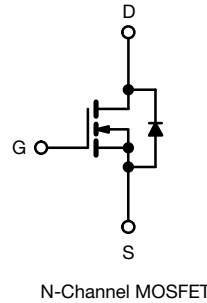
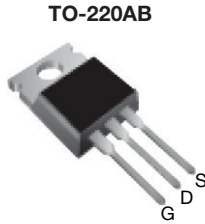


Power MOSFET



FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptable power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Two transistor forward
- Half bridge
- Full bridge

PRODUCT SUMMARY	
V_{DS} (V)	500
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 3.0
Q_g (Max.) (nC)	17
Q_{gs} (nC)	4.3
Q_{gd} (nC)	8.5
Configuration	Single


ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF820APbF
Lead (Pb)-free and halogen-free	IRF820APbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	500	V	
Gate-source voltage		V_{GS}	± 30		
Continuous drain current	V_{GS} at 10 V	I_D	$T_C = 25\text{ }^\circ\text{C}$	2.5	A
			$T_C = 100\text{ }^\circ\text{C}$	1.6	
Pulsed drain current ^a		I_{DM}	10		
Linear derating factor			0.40	W/ $^\circ\text{C}$	
Single pulse avalanche energy ^b		E_{AS}	140	mJ	
Repetitive avalanche current ^a		I_{AR}	2.5	A	
Repetitive avalanche energy ^a		E_{AR}	5.0	mJ	
Maximum power dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	50	W	
Peak diode recovery dV/dt ^c		dV/dt	3.4	V/ns	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$	
Soldering recommendations (peak temperature) ^d	For 10 s		300 ^d		
Mounting torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 45\text{ mH}$, $R_g = 25\text{ }^\circ\Omega$, $I_{AS} = 2.5\text{ A}$ (see fig. 12)
- $I_{SD} \leq 2.5\text{ A}$, $dI/dt \leq 270\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	2.5	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.60	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.5	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 1.5\text{ A}^b$	-	-	3.0	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 1.5\text{ A}^b$		1.4	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	340	-	pF
Output capacitance	C_{oss}			-	53	-	
Reverse transfer capacitance	C_{rss}			-	2.7	-	
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$		-	490	-	
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$		-	15	-	
Effective output capacitance	$C_{oss\text{ eff.}}$	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ V to } 400\text{ V}^c$		-	28	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 2.5\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	17	nC
Gate-source charge	Q_{gs}			-	-	4.3	
Gate-drain charge	Q_{gd}			-	-	8.5	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 2.5\text{ A}, R_g = 21\text{ }\Omega, R_D = 97\text{ }\Omega$, see fig. 10 ^b		-	8.1	-	ns
Rise time	t_r			-	12	-	
Turn-Off delay time	$t_{d(off)}$			-	16	-	
Fall time	t_f			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	2.5	A
Pulsed diode forward current ^a	I_{SM}			-	-	10	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 2.5\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 2.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	330	500	ns
Body diode reverse recovery charge	Q_{rr}			-	760	1140	nC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

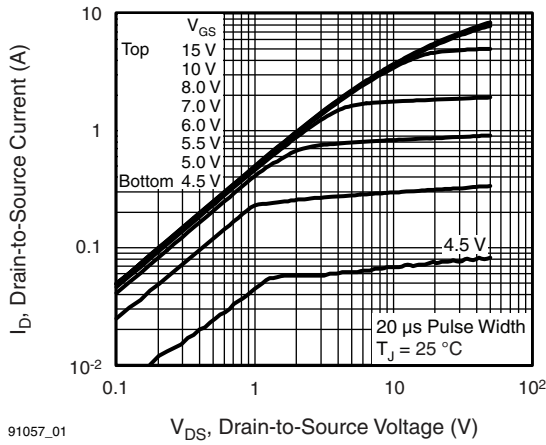


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

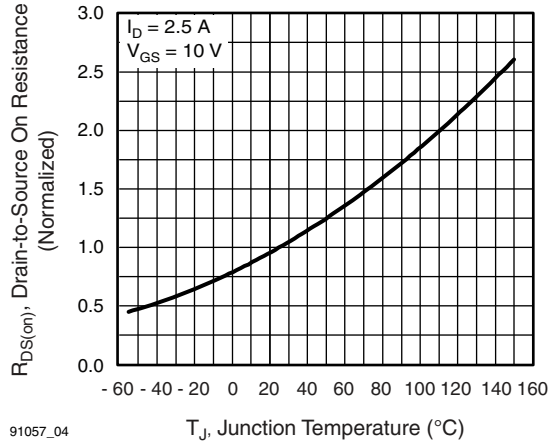


Fig. 4 - Normalized On-Resistance vs. Temperature

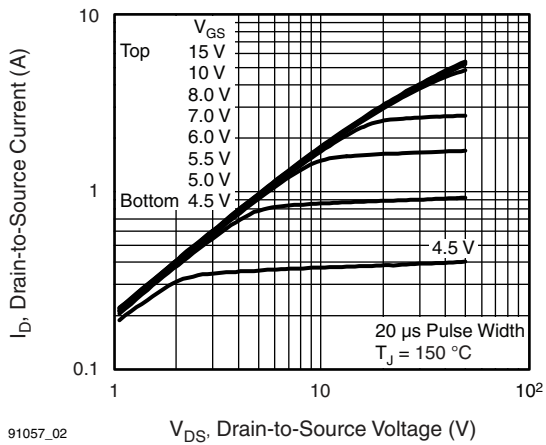


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

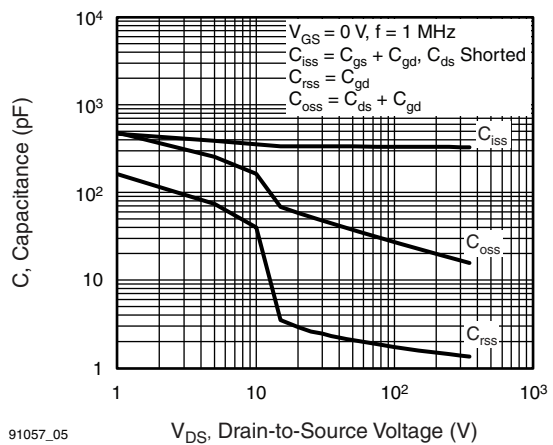


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

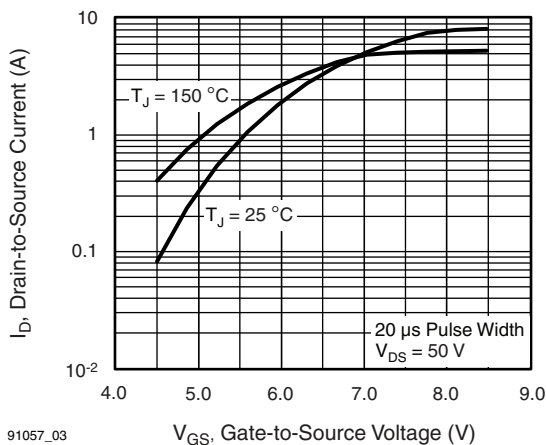


Fig. 3 - Typical Transfer Characteristics

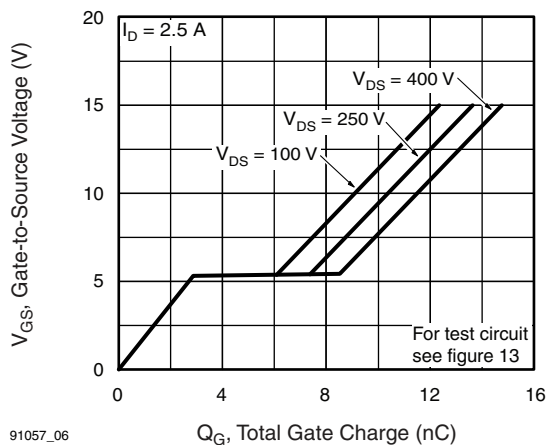
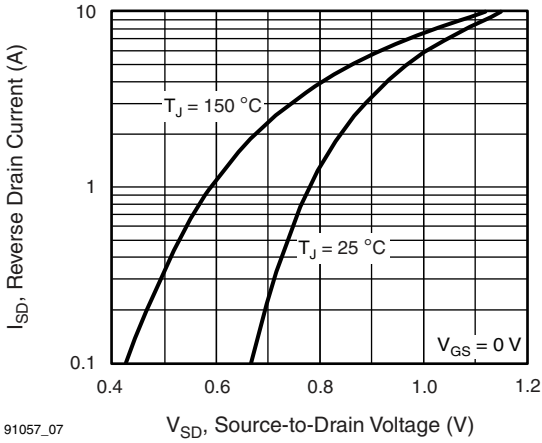
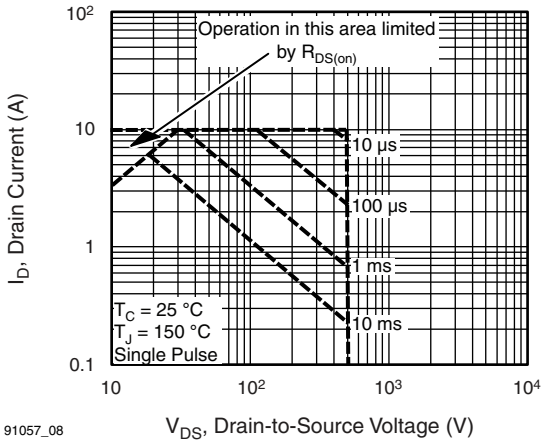


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



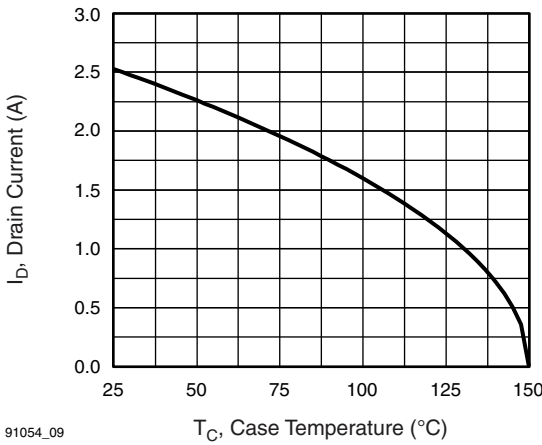
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91057_08

Fig. 8 - Maximum Safe Operating Area



91054_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

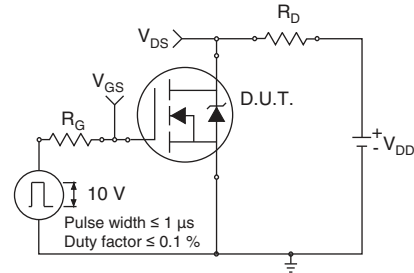


Fig. 10 - Switching Time Test Circuit

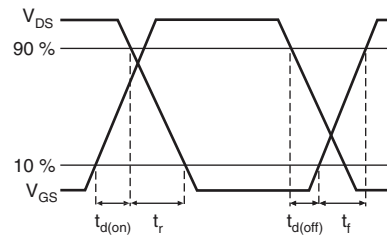


Fig. 11 - Switching Time Waveforms

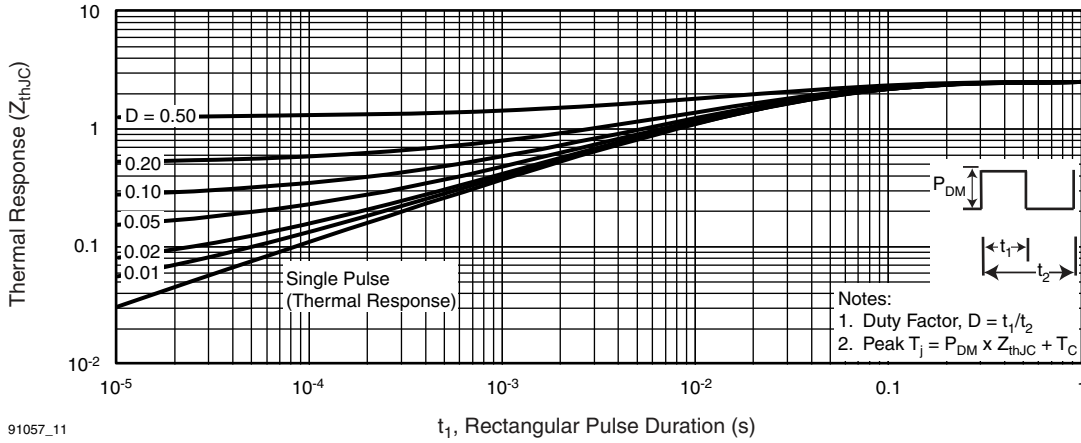


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

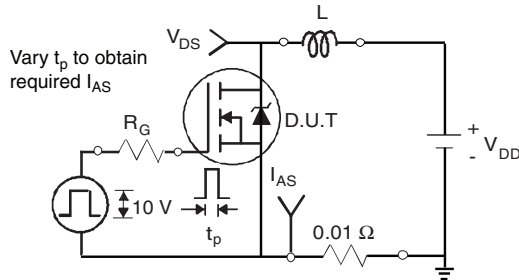


Fig. 13 - Unclamped Inductive Test Circuit

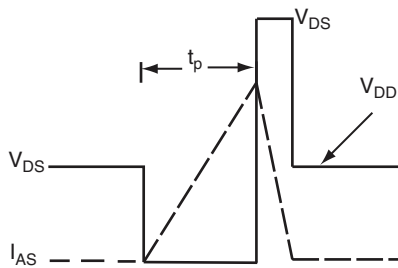


Fig. 14 - Unclamped Inductive Waveforms

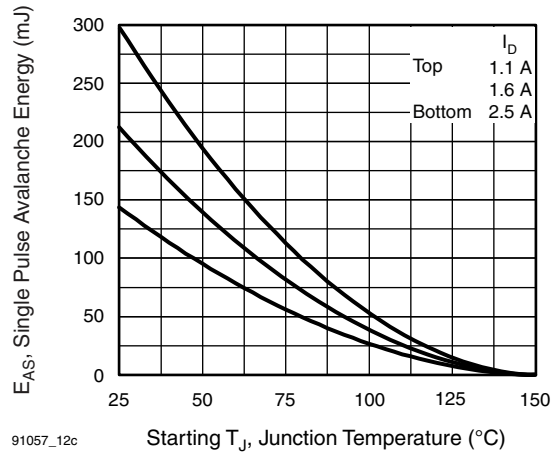


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

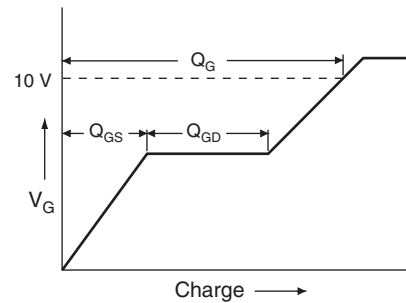
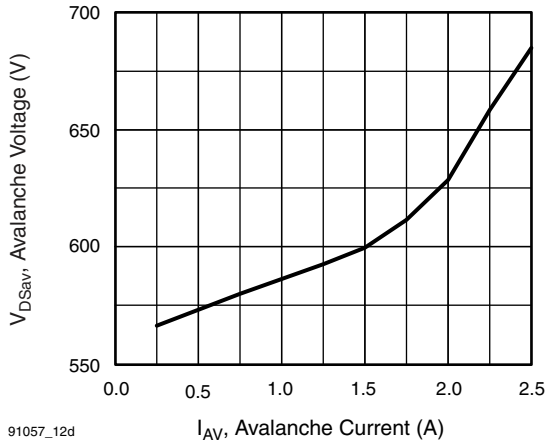


Fig. 16 - Basic Gate Charge Waveform



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Fig. 17 - Typical Drain-to-Source Voltage vs. Avalanche Current

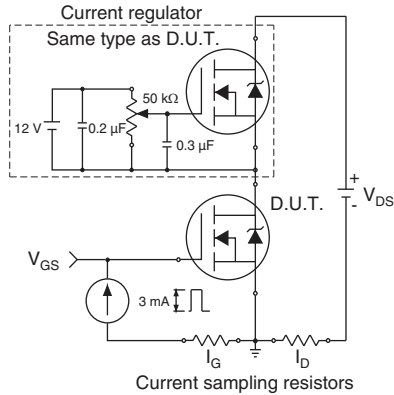
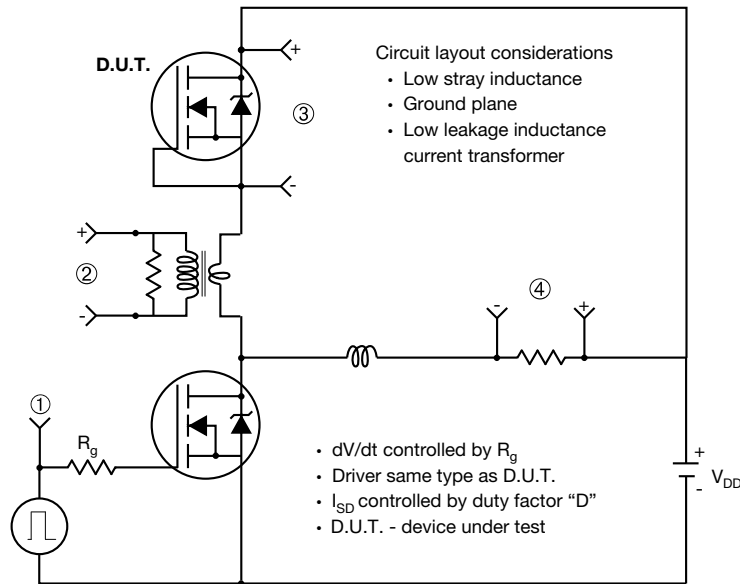


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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